

**R18**

**Code No: 156DF**

**JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD**

**B. Tech III Year II Semester Examinations, January/February - 2025**

**VLSI DESIGN**

**(Electronics and Communication Engineering)**

**Time: 3 Hours**

**Max. Marks: 75**

**Note:** i) Question paper consists of Part A, Part B.

ii) Part A is compulsory, which carries 25 marks. In Part A, Answer all questions.

iii) In Part B, Answer any one question from each unit. Each question carries 10 marks and may have a, b as sub questions.

**PART - A**

**(25 Marks)**

- 1.a) What is a pass transistor? [2]
- b) Mention the advantages of Bi-CMOS circuits. [3]
- c) Mention the importance of scaling. [2]
- d) Why spacing between n-diffusion to p-diffusion is large? [3]
- e) Define Fan out. [2]
- f) Mention the three sources of wiring capacitance. [3]
- g) Mention the applications of counters. [2]
- h) What are the limitations of SRAM? [3]
- i) List out the chip level test techniques in VLSI. [2]
- j) Mention any two differences between PLA and PAL. [3]

**PART - B**

**(50 Marks)**

- 2.a) Explain the CMOS fabrication process with suitable diagrams.
- b) Determine the pull-up to pull-down ratio for an NMOS inverter driven by another NMOS inverter. [5+5]

**OR**

- 3.a) Draw a simple BiCMOS inverter circuit diagram and explain its operation.
- b) Explain the latch-up condition in CMOS Circuits and methods to eliminate it. [5+5]

- 4.a) Discuss in brief the effects and limitations of scaling on Substrate doping and interconnect and contact resistances.
- b) Discuss the methodology to be followed in layout design. [5+5]

**OR**

- 5.a) Discuss in brief the effects and limitations of scaling on Logic levels and Supply voltage.
- b) Mention different choices of layers to be considered in wiring a circuit. [5+5]

- 6.a) Draw the circuit of a logic gate using DCVS logic and explain the operation.
- b) Explain the effect of wiring capacitance on the performance of VLSI circuits. [5+5]

**OR**

- 7.a) Draw the circuit of a logic gate using pseudo NMOS logic and explain the operation.
- b) Write a brief note on Resistive interconnect delay. [5+5]

QA QA QA QA QA QA QA G

8.a) Explain the design and operation of a Multiplier.

b) Explain the design and operation of ROM.

[5+5]

QA QA QA QA QA QA QA G

9.a) Explain the design and operation of a SRAM.

b) Explain the design and operation of an ALU.

[5+5]

10.a) Explain the design approach of a PAL.

b) What is testing? Explain the procedure to test single gates.

[5+5]

**OR**

QA QA QA QA QA QA QA G

11.a) Explain the design approach of a FPGA.

b) Explain any one Chip level test technique.

[5+5]

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QA QA QA QA QA QA QA G

QA QA QA QA QA QA QA G

QA QA QA QA QA QA QA G

QA QA QA QA QA QA QA G

QA QA QA QA QA QA QA G